XA-9967
PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Atsushi HIRAIWA et al.

Appln. No.:

Filed: HEREWITH

For: METHOD FOR FABRICATING SEMICONDUCTOR DEVICES

* * *

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

Sir:

Pursuant to 37 C.F.R. § 1.56, and without any assertion as to materiality or prior art effect, the documents listed on the attached Form PTO-1449 are hereby cited.

Documents AH and AO on the attached List are cited in the specification, on pages 1 and 2, and their relevance is indicated therein.

Respectfully submitted,

NHS:lmb

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October 30, 2003

FORM PTO-1449 LIST OF DOCUMENTS CITED BY APPLICANT	Atty. Docket No. XA-9967	Appln. No.
	Applicant Atsushi HIRAIWA t al.	
	Filing Date Herewith	Group

U.S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Sub-class	Filing Date
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						

FOREIGN PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Country	Class	Sub-class	Translation
	AH	11-177047	7/2/99	Japan			abstract
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

OTHER (including author, title, date, pertinent pages, etc.)

	AO	Ultra Clean Society closing memorial symposium, "toward the new century led by semiconductor", September 24-25, 2000, pp. 42-52.
	AP	Katsuyuki Sekine et al., IEEE Transactions on Electron Devices, "Highly Reliable Ultrathin Silicon Oxide Film Formation at Low Temperature by Oxygen Radical Generated in High-Density Krypton Plasma", Vol. 48, No. 8, August 2001, pp. 1550-1555.
	AQ	Masaki Hirayama et al., IEEE, "Low-Temperature Growth of High-Integrity Silicon Oxide Films by Oxygen Radical Generated in High-Density Krypton Plasma", 1999, pp. 499-502.

Examiner	Date Considered

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.